Docket No.

211836US2SRD RE

IN RE APPLICATION OF: Yasuo OHBA, et al.

FILED:

SERIAL NO: 09/915,710 July 27, 2001

FOR:

AND METHOD OF FABRICATING THE SAME SEMICONDUCTOR DEVICE

COMMISSIONER FOR PATENT

ALEXANDRIA, VIRGINIA 22

SIR:

Transmitted herewith is a supplement amendment in the above-identified application.

☐ No additional fee is required

☐ Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.

Additional documents filed herewith:

Attachments 1 and 2, Copy of the Amendment filed on July 20, 2002 (along with a copy of the date-stamped filing receipt)

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS		RATE		CALCULATIONS
TOTAL	91	MINUS	71	20	х	\$18	=	\$360.00
INDEPENDENT	21	MINUS	20	1	х	\$84	=	\$84.00
		☐ MULTIPLE DEPENDENT CLAIMS			+	\$280	=	\$0.00
		TOTAL OF ABOVE CALCULATIONS						\$444.00
		☐ Reduction by 50% for filing by Small Entity					\$0.00	
		☐ Recordation of Assignment + \$				\$40	=	\$0.00
						тот	AL	\$444.00

- A check in the amount of \$444.00 is attached.
- Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.
- If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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211836US-2SRD RE

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

N RE APPLICATION OF

YASUO OHBA ET AL.

: EXAMINER: JACKSON, J.

SERIAL NO: 09/915,710

FILED: JULY 27, 2001

: GROUP ART UNIT: 2815

SEMICONDUCTOR DEVICE AND FOR:

METHOD OF FABRICATING THE

SAME

SUPPLEMENTAL AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

Supplemental to the response filed July 30, 2002 and responsive to the Office Action dated March 18, 2002, and the Communication dated July 11, 2002, please amend the aboveidentified application as follows:

IN THE CLAIMS

Please amend the claims to read as follows:

1. (Arrended) A semiconductor device comprising:

a buffer semiconductor layer made of $Al_{1-s-t}Ga_sIn_tN$ ($0 \le s \le 1$, $0 \le t \le 1$, $s+t \le 1$) and having a number of pinholes formed therein;

a thermal distortion reducing layer made of $A1_{1-u-v}Ga_uIn_vN$ ($0 \le u \le 1$, $[0 \le v \le 1]$ $0 < v \le 1$, u+v≤1) formed on said buffer sergiconductor layer and having a different chemical formula from that of said buffer semiconductor layer;

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